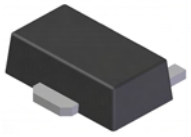
NEW PRODUCT

DXT2222A

NPN SURFACE MOUNT TRANSISTOR

Features

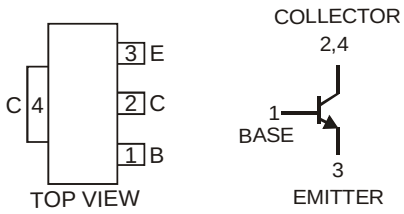
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DXT2907A)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



SOT89-3L

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Peak Pulse Current	I_{CM}	800	mA
Continuous Collector Current	I_C	600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T_A = 25°C	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T_A = 25°C	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Notes:
1. No purposefully added lead.
2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

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Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	75	—	V	I_C = 10μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	I_C = 10mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	I_E = 10μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	10	nA μA	V_{CB} = 60V, I_E = 0 V_{CB} = 60V, I_E = 0, T_A = 150°C
Collector Cutoff Current	I_{CEX}	—	10	nA	V_{CE} = 60V, $V_{EB(OFF)}$ = 3.0V
Emitter Cutoff Current	I_{EBO}	—	10	nA	V_{EB} = 3.0V, I_C = 0
Base Cutoff Current	I_{BL}	—	20	nA	V_{CE} = 60V, $V_{EB(OFF)}$ = 3.0V
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h_{FE}	35 50 75 100 40 35 50	— — — 300 — — —	—	I_C = 100μA, V_{CE} = 10V I_C = 1.0mA, V_{CE} = 10V I_C = 10mA, V_{CE} = 10V I_C = 150mA, V_{CE} = 10V I_C = 500mA, V_{CE} = 10V I_C = 10mA, V_{CE} = 10V, T_A = -55°C I_C = 150mA, V_{CE} = 1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	— —	0.3 1.0	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.6 —	1.2 2.0	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	8	pF	V_{CB} = 10V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	25	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = 20V, I_C = 20mA, f = 100MHz
Noise Figure	NF	—	4.0	dB	V_{CE} = 10V, I_C = 150μA, R_S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	10	ns	V_{CC} = 30V, I_C = 150mA,
Rise Time	t_r	—	25	ns	$V_{EB(off)}$ = 0.5V, I_{B1} = 15mA
Storage Time	t_s	—	225	ns	V_{CC} = 30V, I_C = 150mA,
Fall Time	t_f	—	60	ns	I_{B1} = I_{B2} = 15mA

Notes: 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

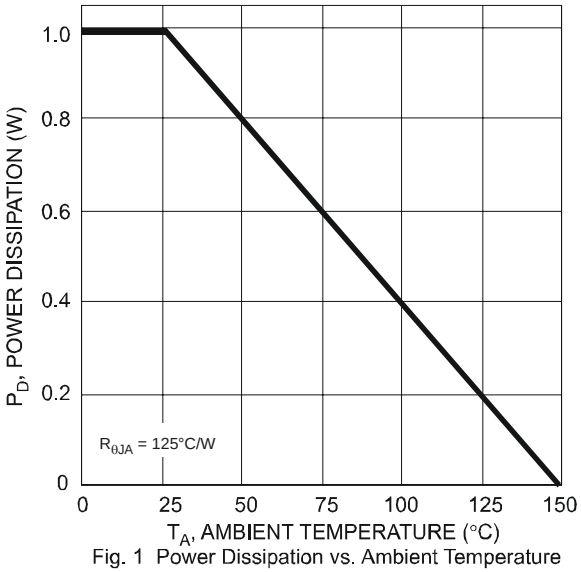

Fig. 1 Power Dissipation vs. Ambient Temperature

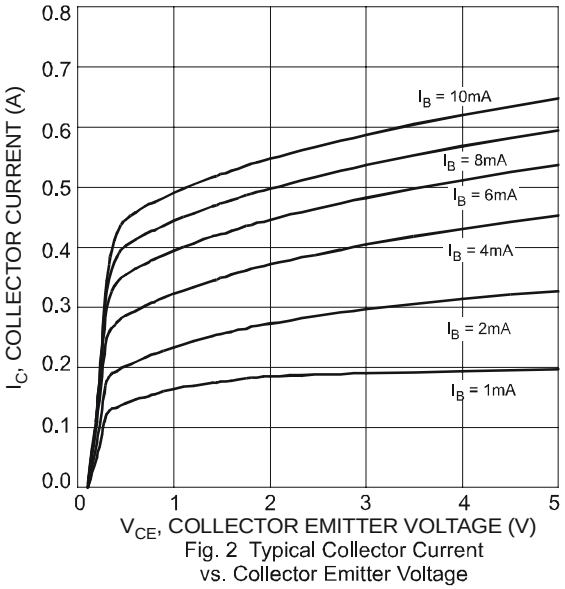

Fig. 2 Typical Collector Current vs. Collector Emitter Voltage

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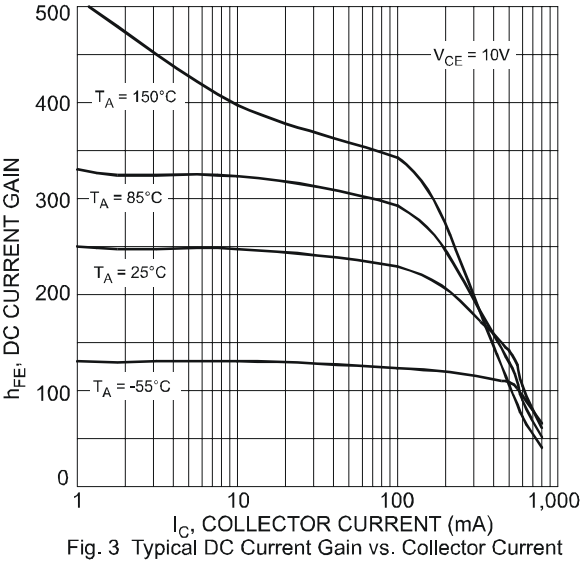


Fig. 3 Typical DC Current Gain vs. Collector Current

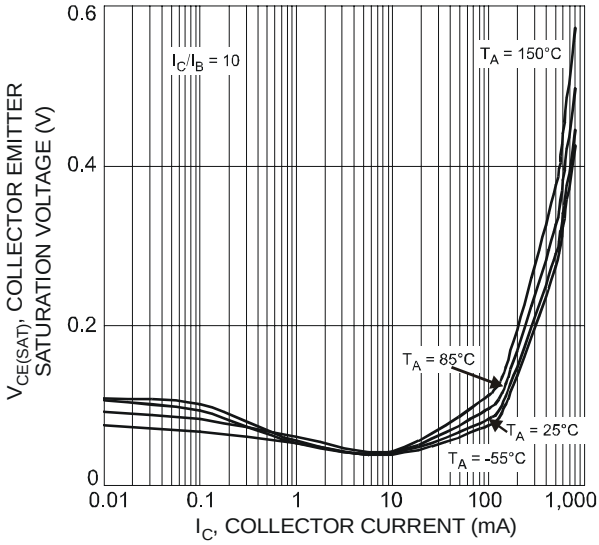


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

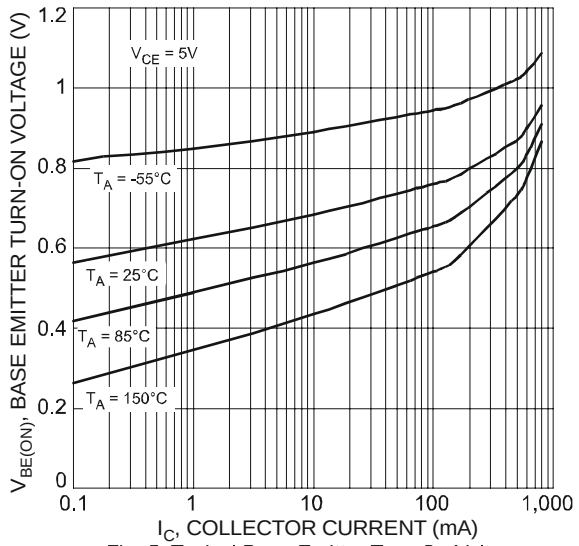


Fig. 5 Typical Base Emitter Turn-On Voltage vs. Collector Current

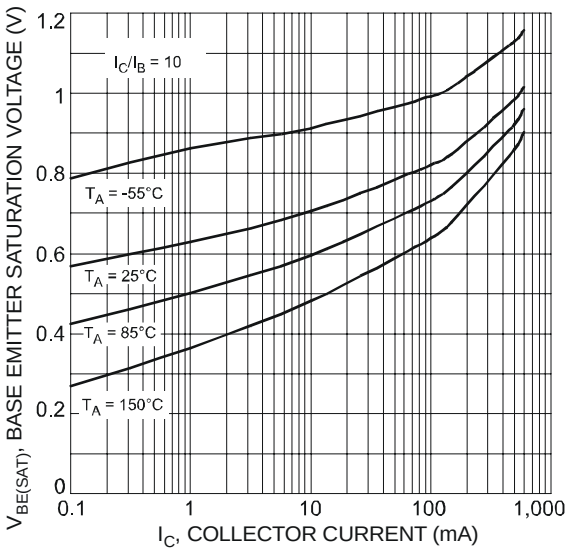


Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current

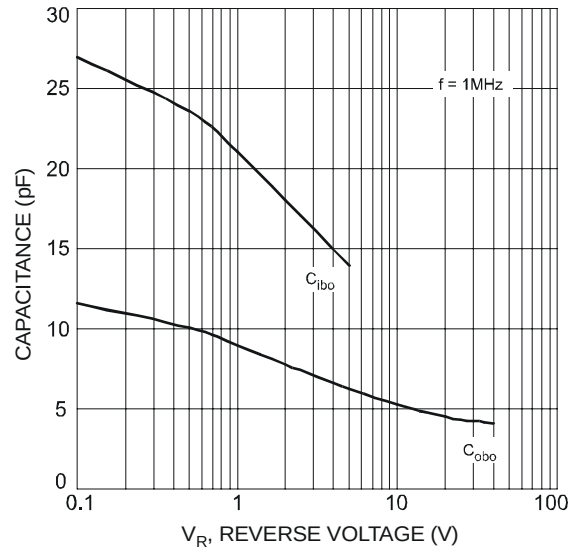


Fig. 7 Typical Capacitance Characteristics

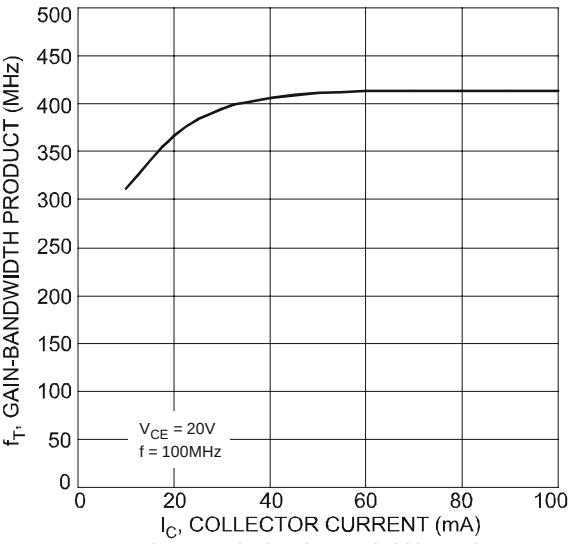


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

NEW PRODUCT

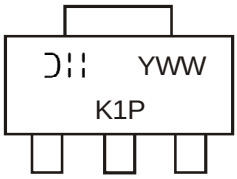
Ordering Information (Note 5)

Device	Packaging	Shipping
DXT2222A-13	SOT89-3L	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

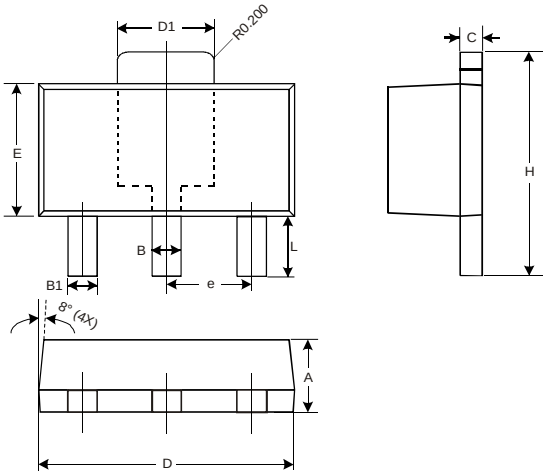
Marking Information

(Top View)



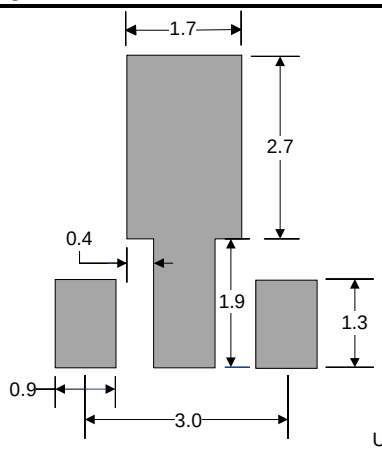
= Manufacturer's code marking
K1P = Product Type Marking Code
YWW = Date Code Marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



Unit: mm